2SK1808

Silicon N-Channel MOS FET

HITACHI

ADE-208-1322 (Z) 1st. Edition Mar. 2001

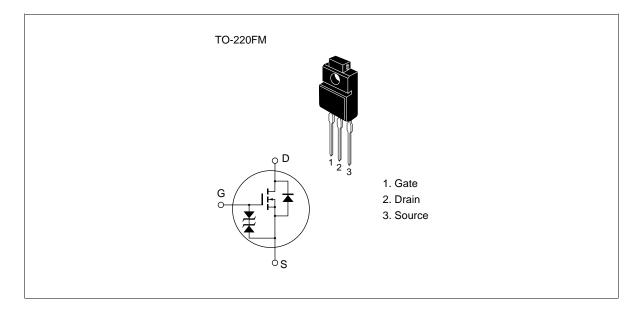
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switchingregulator, DC-DC converter

Outline





2SK1808

Absolute Maximum Ratings $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	900	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	4	A
Drain peak current	I _{D(pulse)} *1	10	A
Body to drain diode reverse drain current	I _{DR}	4	A
Channel dissipation	Pch*2	35	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes 1. PW \leq 10 μ s, duty cycle \leq 1 %

2. Value at Tc = 25 °C

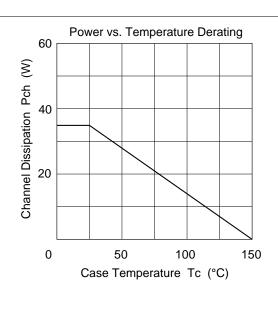
Electrical Characteristics ($Ta = 25^{\circ}C$)

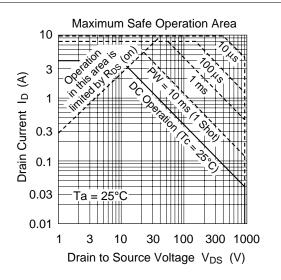
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	900	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±30	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	250	μΑ	$V_{DS} = 720 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	_	3.0	V	$I_{\rm D} = 1 \text{ mA}, V_{\rm DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	_	3.0	4.0	Ω	$I_D = 2 A$ $V_{GS} = 10 V^{*1}$
Forward transfer admittance	y _{fs}	1.7	2.7	_	S	$I_D = 2 A$ $V_{DS} = 10 V^{*1}$
Input capacitance	Ciss	_	740	_	pF	V _{DS} = 10 V
Output capacitance	Coss	_	305	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	150	_	pF	f = 1 MHz
Turn-on delay time	$t_{\text{d(on)}}$	_	15	_	ns	$I_D = 2 A$
Rise time	t _r	_	60	_	ns	V _{GS} = 10 V
Turn-off delay time	t _{d(off)}	_	100	_	ns	$R_L = 15 \Omega$
Fall time	t _f		80		ns	
Body to drain diode forward voltage	V_{DF}		0.9		V	$I_F = 4 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t _{rr}		800	_	ns	$I_F = 4 \text{ A}, V_{GS} = 0,$ $di_F / dt = 100 \text{ A} / \mu \text{s}$

Note 1. Pulse Test

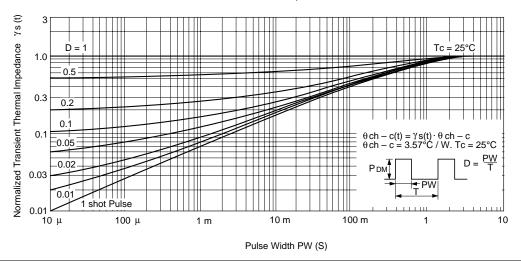
See characteristic curves of 2SK1340

2SK1808

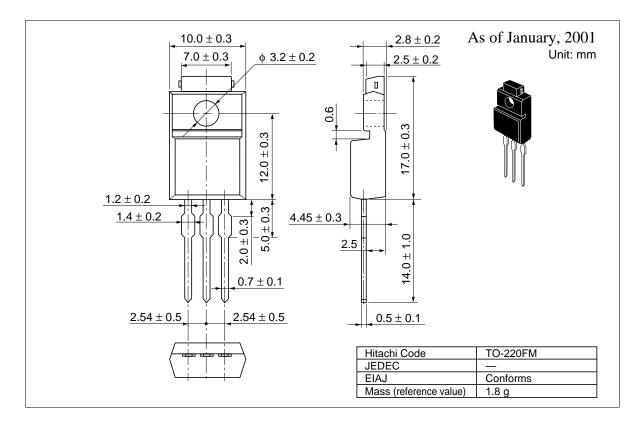




Normalized Transient Thermal Impedance vs. Pulse Width



Package Dimensions



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